

Vishay Siliconix

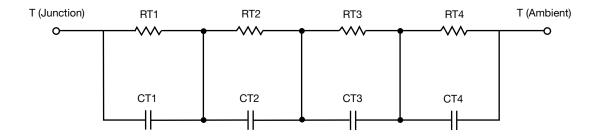
R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

R-C THERMAL MODEL FOR TANK CONFIGURATION



C VALUES FOR TANK CONFIGURATION THERMAL RESISTANCE (°C/W)					
RT1	12.4277	107.8425m	N/A		
RT2	3.3395	66.0681m	N/A		
RT3	2.8888	198.7128m	N/A		
RT4	21.4302	28.9048m	N/A		
	THERMAL CAPAC	ITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	9.3572	4.1489m	N/A		
CT2	50.3305	148.5188m	N/A		
CT3	346.2915m	10.6291m	N/A		
CT4	3.3933	851.5517m	N/A		

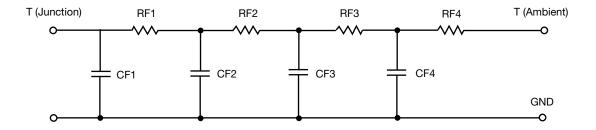
Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

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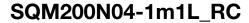
R-C THERMAL MODEL FOR FILTER CONFIGURATION



R-C VALUES FOR FILTER CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	2.7203	241.6174m	N/A			
RF2	11.3843	116.5744m	N/A			
RF3	16.8475	40.0255m	N/A			
RF4	9.0628	3.1880m	N/A			
	THERMAL CAPAC	CITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	219.0253m	3.1848m	N/A			
CF2	1.5881	24.4421m	N/A			
CF3	906.7064m	317.5989m	N/A			
CF4	3.9043	38.7959m	N/A			

Note

• n/a indicates not applicable





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